

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	675	257/324.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/24 12:51
S2	1	("20030155582").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/23 18:09
S3	1	("6858899").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/23 18:09
S4	1	("20050014322").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/23 18:09
S5	1	("6849905").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/23 18:09
S6	1	("6737675").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/23 18:10
S7	1	("6674138").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/23 18:12
S8	6	S2 S3 S4 S5 S6 S7	US-PGPUB; USPAT	OR	OFF	2005/02/23 18:12
S9	97	(sonos near3 transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/25 16:23
S10	17	(blocking near2 dielectric) and (tunneling near2 dielectric) and ((storage or charge) near3 dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/26 16:09
S11	1	("6469343").PN.	USPAT	OR	OFF	2005/02/24 12:51
S12	0	(sonos near3 transistor) and (gate with (tungsten or w)) and (substrate with (ploysilicon or poly-silicon)) and (mono-crystalline or monocrystalline)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/27 10:25
S13	0	(sonos near3 transistor) and (gate with (tungsten or w)) and (substrate with (ploysilicon or poly-silicon))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/25 16:26

S14	0	(sonos near3 transistor) and (substrate with (polysilicon or poly-silicon))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/25 16:26
S15	23	(sonos near3 transistor) and (substrate with (polysilicon or poly-silicon))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/25 16:33
S16	3	(sonos near3 transistor) and (gate with (tungsten or w)) and (substrate with (polysilicon or poly-silicon)) and (mono-crystalline or monocrystalline)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/25 16:34
S17	32	(sonos near10 transistor) and (substrate with (polysilicon or poly-silicon))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/26 15:22
S18	3	(sonos near10 transistor) and (gate with (tungsten or w)) and (substrate with (polysilicon or poly-silicon)) and (mono-crystalline or monocrystalline)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/25 16:34
S19	3	(ono near10 transistor) and (gate with (tungsten or w)) and (substrate with (polysilicon or poly-silicon)) and (mono-crystalline or monocrystalline)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/25 16:35
S20	331	(transistor) and (gate with (tungsten or w)) and (substrate with (polysilicon or poly-silicon)) and (mono-crystalline or monocrystalline)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/25 16:35
S21	5	S20 and sonos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/25 16:35

S22	12	(US-20020100931-\$ or US-20030071304-\$ or US-20030216000-\$ or US-20040007734-\$ or US-20040062118-\$ or US-20040262702-\$).did. or (US-6469343-\$ or US-6605839-\$ or US-6674138-\$ or US-6677640-\$ or US-6682973-\$ or US-6709928-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/03/01 16:56
S23	2	S22 and (polysilicon and (monocrystalline or (single near3 crystalline))) and (tungsten or w)	US-PGPUB; USPAT	OR	OFF	2005/03/01 17:03
S24	6	S22 and (tungsten or w)	US-PGPUB; USPAT	OR	OFF	2005/03/01 17:03
S25	0	S22 and ((tungsten or w) near5 gate)	US-PGPUB; USPAT	OR	OFF	2005/03/01 17:04
S26	165	((tungsten or w) near5 gate) and (inverted near3 transistor)	US-PGPUB; USPAT	OR	OFF	2005/03/01 17:35
S27	44	((tungsten or w) near5 (back near3 gate))	US-PGPUB; USPAT	OR	OFF	2005/03/01 17:36
S28	252	(sonos) and (substrate with (polysilicon or poly-silicon))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/26 15:22
S29	18	S28 and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/26 15:22
S30	31	(blocking near3 dielectric) and (tunneling near3 dielectric) and ((storage or charge) near4 dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/26 19:28
S31	1	"20020033501".PN.	US-PGPUB	OR	OFF	2005/09/26 16:47
S32	1	"20020028541".PN.	US-PGPUB	OR	OFF	2005/09/26 16:47
S33	1	"20020024092".PN.	US-PGPUB	OR	OFF	2005/09/26 16:47
S34	1	"20020020890".PN.	US-PGPUB	OR	OFF	2005/09/26 16:47
S35	1	"20020000592".PN.	US-PGPUB	OR	OFF	2005/09/26 16:47
S36	1	"20010055838".PN.	US-PGPUB	OR	OFF	2005/09/26 16:47
S37	1	"20010052615".PN.	US-PGPUB	OR	OFF	2005/09/26 16:47
S38	1	"20010046738".PN.	US-PGPUB	OR	OFF	2005/09/26 16:47
S39	1	"20010041434".PN.	US-PGPUB	OR	OFF	2005/09/26 16:48

S40	1	"20010041250".PN.	US-PGPUB	OR	OFF	2005/09/26 16:48
S41	1	"20010030340".PN.	US-PGPUB	OR	OFF	2005/09/26 16:48
S42	1	"6660588".PN.	USPAT; USOCR	OR	OFF	2005/09/26 16:48
S43	1	"6630383".PN.	USPAT; USOCR	OR	OFF	2005/09/26 16:48
S44	1	"6617639".PN.	USPAT; USOCR	OR	OFF	2005/09/26 16:48
S45	1	"6593624".PN.	USPAT; USOCR	OR	OFF	2005/09/26 16:48
S46	1	"6348380".PN.	USPAT; USOCR	OR	OFF	2005/09/26 16:48
S47	1	"6326268".PN.	USPAT; USOCR	OR	OFF	2005/09/26 16:48
S48	1	"6319775".PN.	USPAT; USOCR	OR	OFF	2005/09/26 16:48
S49	1	"6313503".PN.	USPAT; USOCR	OR	OFF	2005/09/26 16:48
S50	1	"6301155".PN.	USPAT; USOCR	OR	OFF	2005/09/26 16:48
S51	1	"6297143".PN.	USPAT; USOCR	OR	OFF	2005/09/26 16:48
S52	1	"6288419".PN.	USPAT; USOCR	OR	OFF	2005/09/26 16:48
S53	1	"6285596".PN.	USPAT; USOCR	OR	OFF	2005/09/26 16:48
S54	1	"6285586".PN.	USPAT; USOCR	OR	OFF	2005/09/26 16:48
S55	1	"6248635".PN.	USPAT; USOCR	OR	OFF	2005/09/26 16:48
S56	1	"6191459".PN.	USPAT; USOCR	OR	OFF	2005/09/26 16:48
S57	1	"6185122".PN.	USPAT; USOCR	OR	OFF	2005/09/26 16:48
S58	1	"5889302".PN.	USPAT; USOCR	OR	OFF	2005/09/26 16:48
S59	1	"5691552".PN.	USPAT; USOCR	OR	OFF	2005/09/26 16:48
S60	1	"5306935".PN.	USPAT; USOCR	OR	OFF	2005/09/26 16:48
S61	30	S31 S32 S33 S34 S35 S36 S37 S38 S39 S40 S41 S42 S43 S44 S45 S46 S47 S48 S49 S50 S51 S52 S53 S54 S55 S56 S57 S58 S59 S60	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/26 17:20

S62	1927	monos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/26 17:20
S63	281	monos near5 transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/26 17:20
S64	154	S63 and ((poly near2 silicon) or polysilicon or poly-silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/26 17:20
S65	1	("6881994").PN.	USPAT	OR	OFF	2005/09/26 19:05
S66	32	(blocking near3 insulat\$3) and (tunneling near3 insulat\$3) and ((storage or charge or trapping) near4 insulat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/26 19:29
S67	31	(blocking near3 dielectric) and (tunneling near3 dielectric) and ((storage or charge) near4 dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/26 19:29
S68	27	S66 not S67	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/26 19:29
S69	476	"257"/\$.ccls. and sonos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 14:52
S70	137	((polysilicon or (poly near2 silicon) or poly-silicon) near5 substrate) WITH advantage) and (semiconductor or ic or die or chip or (integrated adj circuit))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 16:10

S71	1	S70 and sonos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 14:55
S72	72	((polysilicon or (poly near2 silicon) or poly-silicon) near2 substrate) and sonos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 15:36
S73	3	S72 and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 15:36
S74	18	(US-20020100931-\$ or US-20030071304-\$ or US-20030216000-\$ or US-20040007734-\$ or US-20040062118-\$ or US-20040069990-\$ or US-20040262702-\$ or US-20030194853-\$ or US-20040124415-\$).did. or (US-6133605-\$ or US-6469343-\$ or US-6605839-\$ or US-6674138-\$ or US-6677640-\$ or US-6682973-\$ or US-6709928-\$ or US-6797604-\$ or US-6858899-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/09/28 16:09
S75	16	S74 and (polysilicon or (poly near2 silicon) or poly-silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 16:30
S76	54	"257"/\$6.ccls. and (monolithic near3 dimensional near3 array)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 16:34
S77	1	S76 and (situ near3 generation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 17:31

S78	18	sonos and S76	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 16:34
S79	759	257/324.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 17:31
S80	174	257/325.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 17:31
S81	777	257/411.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 17:31
S82	336	438/216.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 17:31
S83	519	438/261.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 17:31
S84	2203	S79 S80 S81 S82 S83	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 17:31
S85	2200	S84 not S70	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 17:31

S86	2184	S85 not S72	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 17:32
S87	358	(transistor) and (gate with (tungsten or w)) and (substrate with (polysilicon or poly-silicon)) and (mono-crystalline or monocrystalline)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 17:33
S88	2180	S86 not S87	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 17:33
S89	252	(sonos) and (substrate with (polysilicon or poly-silicon))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 17:33
S90	2142	S88 not S89	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 17:33
S91	282	monos near5 transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 17:33
S92	243	S89 not S91	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 17:33
S93	2088	S90 not S91	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 17:33



S94	1929	monos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 17:33
S95	2017	S93 not S94	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/28 17:34